In the Claims

Please cancel Claims 2-4,7-9 and 11-13 without prejudice.

Please amend Claims 1,5 and 10.

Listing of Claims

1. (currently amended) A method of seasoning a process chamber having interior surfaces to reduce the formation of silicon residues on said interior surfaces in a subsequent silicon plasma deposition process, comprising the steps of:

cleaning said process chamber according to a cleaning process comprising a chlorine containing etchant to remove silicon residues from said chamber; and

providing a seasoning film ~~selected from the group consisting of silicon nitride,~~ comprises silicon carbide~~, and silicon dioxide~~ on said interior surfaces of said process chamber ~~comprising~~ by introducing precursor gases ~~selected from the group consisting of silane, dichlorosilane, and~~ comprises trimethylsilane and carbon dioxide into said process chamber at a pressure of from about 10 Torr to about 760 Torr.

Claims 2-4 (canceled)

5. (currently amended)) A method of seasoning a chemical vapor deposition chamber having interior surfaces and a gas distribution plate to reduce the formation of silicon residues on

said interior surfaces and said gas distribution plate in a subsequent silicon plasma deposition process, comprising the steps of:

cleaning said chamber according to a cleaning process comprising a chlorine containing etchant gas to remove silicon residues from said chamber; and

providing a seasoning film ~~selected from the group consisting of silicon nitride,~~ comprises silicon carbide~~, and silicon dioxide~~ having a thickness of from about 2 μm to about 10 μm on said interior surfaces and said gas distribution plate of said chamber ~~comprising~~ by introducing precursor gases ~~selected from the group consisting of silane, dichlorosilane, and~~ comprises trimethylsilane and carbon dioxide into said process chamber at a chamber pressure of from about 10 Torr to about 760 Torr at a temperature from about 500 degrees C to about 700 degrees C.

Claims 6-9 (canceled)

10. (currently amended) A method of seasoning a chemical vapor deposition chamber having interior surfaces and a gas distribution plate to reduce the formation of silicon residues on

said interior surfaces and said gas distribution plate in a subsequent silicon plasma deposition process, comprising the steps of:

cleaning said chamber according to a cleaning process comprising a chlorine containing etchant gas to remove silicon residues from said chamber; and

providing a seasoning film ~~selected from the group consisting of silicon nitride,~~ comprises silicon carbide~~, and silicon dioxide~~ having a thickness of from about 2 μm to about 10 μm on said interior surfaces and said gas distribution plate of said chamber comprising introducing precursor gases ~~selected from the group consisting of silane, dichlorosilane, and~~ comprises trimethylsilane and carbon dioxide into said process chamber at a chamber pressure of from about 10 Torr to about 760 Torr at a temperature from about 500 degrees C to about 700 degrees C and a process time of from about 0.5 minutes to about 10 minutes.

Claims 11-14 (canceled)

15. (previously presented) The method of claim 1, further comprising the step of depositing a silicon layer on a substrate within said chamber according to a plasma deposition process.

16. (previously presented) The method of claim 15, wherein said silicon comprises amorphous silicon.

17. (canceled)

18. (previously presented) The method of claim 5, further comprising the step of depositing a silicon layer on a substrate within said chamber according to a plasma deposition process.

19. (canceled)

20. (previously presented) The method of claim 10, further comprising the step of depositing a silicon layer on a substrate within said chamber according to a plasma deposition process.